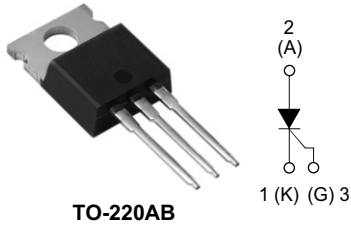




## Phase Control SCR, 10 A



### DESCRIPTION/FEATURES

The 16TTS..PbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.



RoHS\*  
COMPLIANT

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free ("PbF" suffix).

PRODUCT SUMMARY	
$V_T$ at 10 A	< 1.4 V
$I_{TSM}$	200 A
$V_{RRM}$	800/1200 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$ , $T_J = 125\text{ °C}$ , common heatsink of $1\text{ °C/W}$	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
$I_{RMS}$		16	
$V_{DRM}/V_{RRM}$	Range <sup>(1)</sup>	800/1200	V
$I_{TSM}$		200	A
$V_T$	10 A, $T_J = 25\text{ °C}$	1.4	V
dV/dt		500	V/ $\mu$ s
dI/dt		150	A/ $\mu$ s
$T_J$	Range	- 40 to 125	°C

#### Note

<sup>(1)</sup> For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS			
PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM}/I_{DRM}$ AT 125 °C mA
16TTS08PbF	800	800	10
16TTS12PbF	1200	1200	

\* Pb containing terminations are not RoHS compliant, exemptions may apply

# 16TTS..PbF High Voltage Series



Vishay High Power Products Phase Control SCR, 10 A

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 98\text{ }^\circ\text{C}$ , 180° conduction, half sine wave	10		A
Maximum RMS on-state current	$I_{RMS}$		16		
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied	170		
		10 ms sine pulse, no voltage reapplied	200		
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied	144		$A^2s$
		10 ms sine pulse, no voltage reapplied	200		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	2000		$A^2\sqrt{s}$
Maximum on-state voltage drop	$V_{TM}$	10 A, $T_J = 25\text{ }^\circ\text{C}$	1.4		V
On-state slope resistance	$r_t$	$T_J = 125\text{ }^\circ\text{C}$	24.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$		1.1		V
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$T_J = 25\text{ }^\circ\text{C}$ $T_J = 125\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$		mA
Holding current	$I_H$	Anode supply = 6 V, resistive load, initial $I_T = 1$ A 16TTS08PbF, 16TTS12PbF	-	100	
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load	200		
Maximum rate of rise of off-state voltage	$dV/dt$		500		$V/\mu s$
Maximum rate of rise of turned-on current	$dI/dt$		150		$A/\mu s$

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+ I_{GM}$		1.5	A
Maximum peak negative gate voltage	$- V_{GM}$		10	V
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	90	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	60	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	35	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	3.0	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{Rated value}$	0.2	
Maximum DC gate current not to trigger	$I_{GD}$		2.0	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^\circ\text{C}$	0.9	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	$t_q$		110	



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<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		- 40 to 125	°C
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.3	°C/W
Maximum thermal resistance, junction to ambient	$R_{thJA}$		62	
Typical thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-220AB	16TTS08	
			16TTS12	

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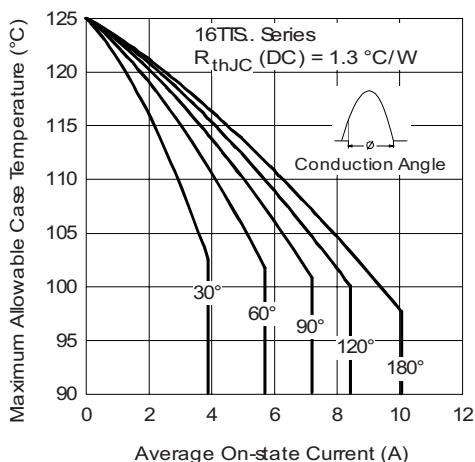


Fig. 1 - Current Rating Characteristics

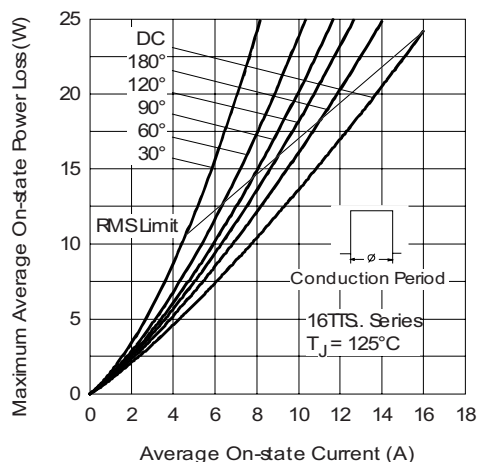


Fig. 4 - On-State Power Loss Characteristics

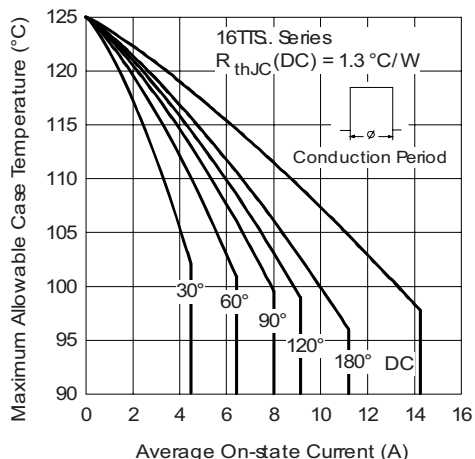


Fig. 2 - Current Rating Characteristics

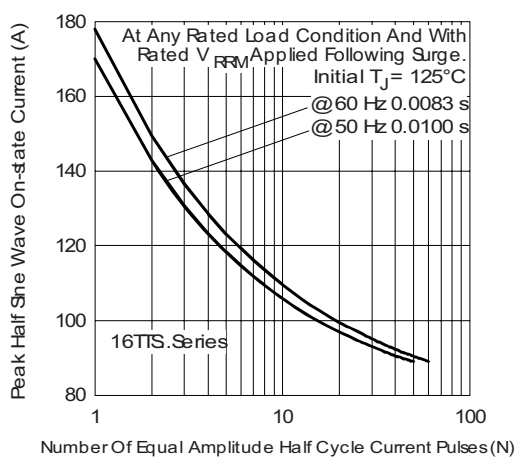


Fig. 5 - Maximum Non-Repetitive Surge Current

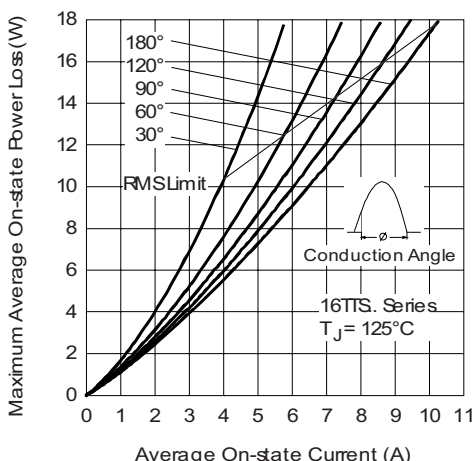


Fig. 3 - On-State Power Loss Characteristics

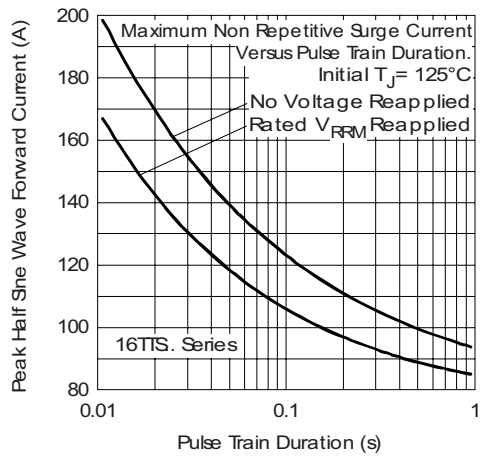


Fig. 6 - Maximum Non-Repetitive Surge Current



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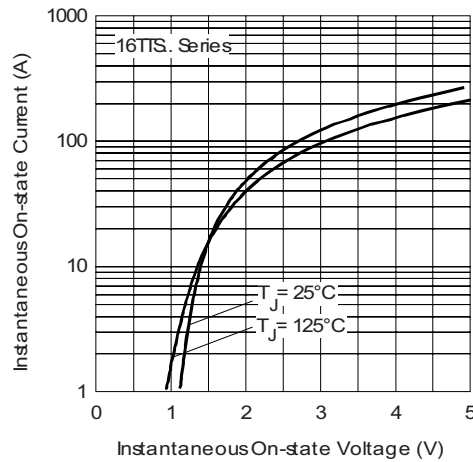


Fig. 7 - On-State Voltage Drop Characteristics

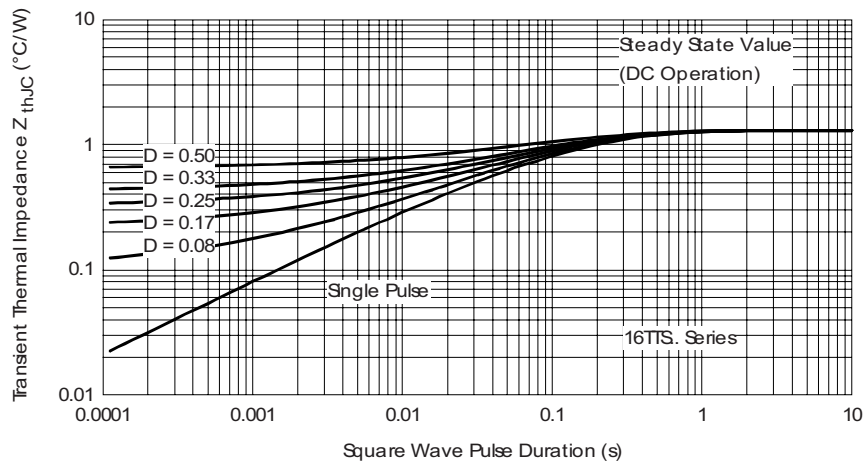


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

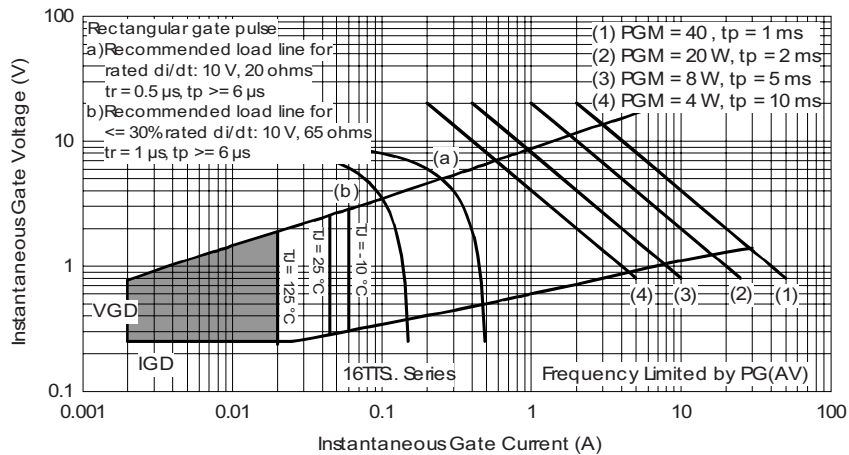


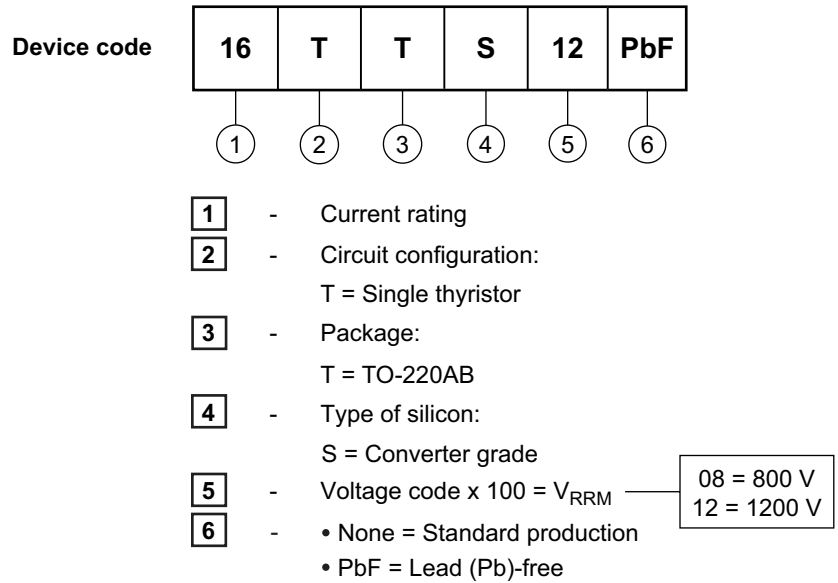
Fig. 9 - Gate Characteristics

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Vishay High Power Products Phase Control SCR, 10 A



## ORDERING INFORMATION TABLE



Note: For higher voltage up to 1600 V contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95222">http://www.vishay.com/doc?95222</a>
Part marking information	<a href="http://www.vishay.com/doc?95225">http://www.vishay.com/doc?95225</a>



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